Features

1) Low on-resistance
2) Fast switching speed
3) Fast reverse recovery
4) Easy to parallel
5) Simple to drive
6) Pb-free lead plating ; RoHS compliant

Parameter	Rating	Units
V_{DS}	**1200**	V
$I_{D\ @\ 25^{\circ}C}$	**102**	A
$R_{DS(on)}$	**21**	m Ω

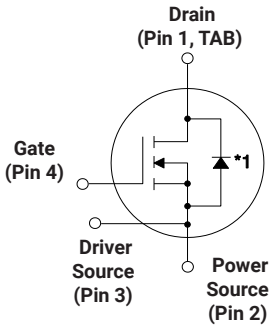
Applications

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating

Inner circuit

TO-247-4

Package



(1) Drain
(2) Power Source
(3) Driver Source
(4) Gate

*1 Body Diode

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	V_{GS} = 0 V, I_D = 100 µA	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC (f >1 Hz)	
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	
I_D	Continuous Drain Current	102	A	V_{GS} = 15 V, T_C = 25˚C	
		76		V_{GS} = 15 V, T_C = 100˚C	
$I_{D(pulse)}$	Pulsed Drain Current	200	A	Pulse width t_P limited by T_{jmax}	
P_D	Power Dissipation	472	W	T_C=25˚C, T_J = 175 ˚C	
T_J , T_{stg}	Operating Junction and Storage Temperature	-40 to +175	˚C		
T_L	Solder Temperature	260	˚C	1.6mm (0.063") from case for 10s	

Note (1): When using MOSFET Body Diode V_{GSmax} = -4V/+19V
Note (2): MOSFET can also safely operate at 0/+15 V

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Electrical Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	V_{GS} = 0 V, I_D = 100 μA	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.5	3.6	V	V_{DS} = V_{GS}, I_D = 17.7 mA	
			2.0		V	V_{DS} = V_{GS}, I_D = 17.7 mA, T_J = 175ºC	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	μA	V_{DS} = 1200 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance		21	28	mΩ	V_{GS} = 15 V, I_D = 50 A	
			38			V_{GS} = 15 V, I_D = 50 A, T_J = 175ºC	
g_{fs}	Transconductance		35		S	V_{DS}= 20 V, I_{DS}= 50 A	
			33			V_{DS}= 20 V, I_{DS}= 50 A, T_J = 175ºC	
C_{iss}	Input Capacitance		1620		pF	V_{GS} = 0 V, V_{DS} = 800 V f = 1 MHz V_{AC} = 25 mV	
C_{oss}	Output Capacitance		180				
C_{rss}	Reverse Transfer Capacitance		12				
E_{oss}	C_{oss} Stored Energy		99		μJ		
E_{ON}	Turn-On Switching Energy (SiC Diode FWD)		0.69		mJ	V_{DS} = 800 V, V_{GS} = -4 V/+15 V, I_D = 50 A, $R_{G(ext)}$ = 2.5Ω, L= 157 μH, T_J = 175ºC	
E_{OFF}	Turn Off Switching Energy (SiC Diode FWD)		0.42				
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		1.58		mJ	V_{DS} = 800 V, V_{GS} = -4 V/+15 V, I_D = 50 A, $R_{G(ext)}$ = 2.5Ω, L= 157 μH, T_J = 175ºC	
E_{OFF}	Turn Off Switching Energy (Body Diode FWD)		0.34				
$t_{d(on)}$	Turn-On Delay Time		31		ns	V_{DD} = 800 V, V_{GS} = -4 V/15 V $R_{G(ext)}$ = 2.5 Ω, L= 157 μH	
t_r	Rise Time		36				
$t_{d(off)}$	Turn-Off Delay Time		57				
t_f	Fall Time		14				
$R_{G(int)}$	Internal Gate Resistance		3.3		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		49		nC	V_{DS} = 800 V, V_{GS} = -4 V/15 V I_D = 50 A Per IEC60747-8-4 pg 21	
Q_{gd}	Gate to Drain Charge		50				
Q_g	Total Gate Charge		160				

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.6		V	V_{GS} = -4 V, I_{SD} = 25 A, T_J = 25 °C	
		4.2		V	V_{GS} = -4 V, I_{SD} = 25 A, T_J = 175 °C	
I_S	Continuous Diode Forward Current		90	A	V_{GS} = -4 V, T_C = 25˚C	
$I_{S, pulse}$	Diode pulse Current		200	A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	
t_{rr}	Reverse Recover time	34		ns	V_{GS} = -4 V, I_{SD} = 50 A, V_R = 800 V dif/dt = 2600 A/μs, T_J = 175 °C	
Q_{rr}	Reverse Recovery Charge	988		nC		
I_{rrm}	Peak Reverse Recovery Current	42		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.32	°C/W		
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	40			

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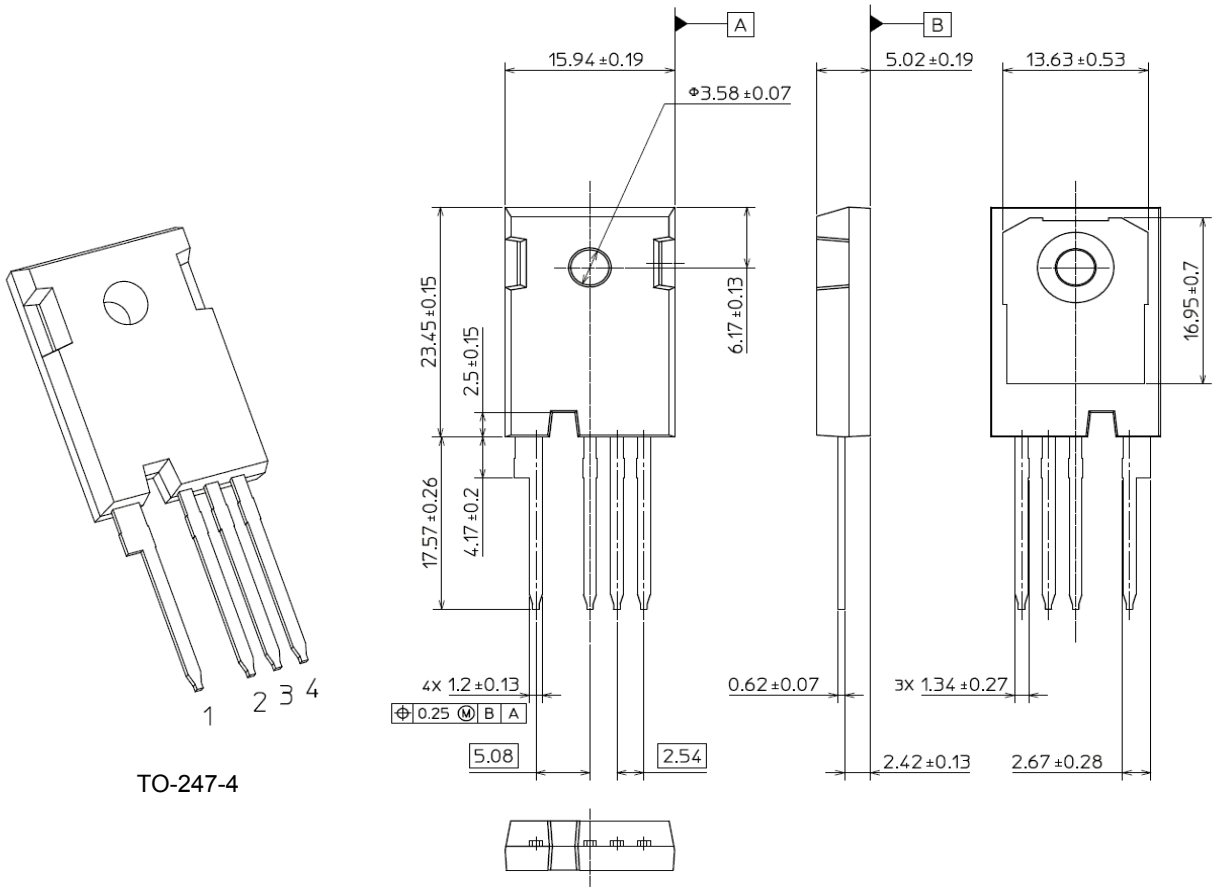
Package Dimensions

Unit: mm



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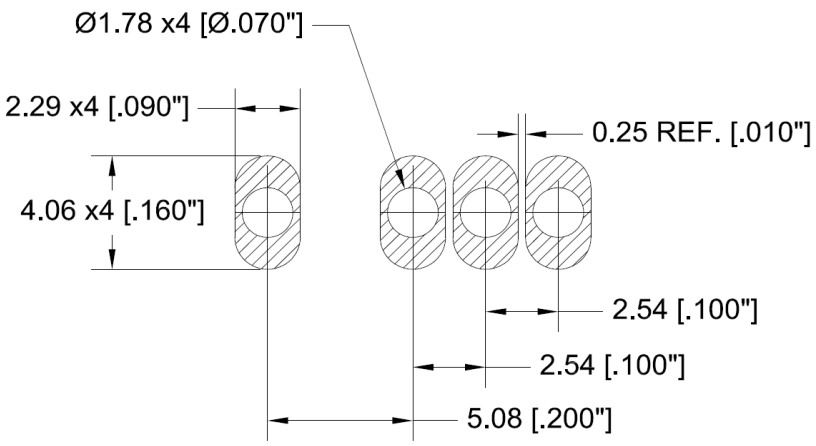

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